

## GBCS SCHEME

4 2 2

17EE34

# Third Semester B.E. Degree Examination, June/July 2019 Analog Electronic Circuits

Time: 3 hrs.

Max. Marks: 100

Note: Answer any FIVE full questions, choosing ONE full question from each module.

### Module-1

- a. With a neat circuit diagram, explain Emitter stabilized bias circuit, write the necessary equation.

  (08 Marks)
  - b. Determine output voltage for the following circuit in Fig.Q.(b). Assume f = 1000 Hz and ideal diode. (06 Marks)

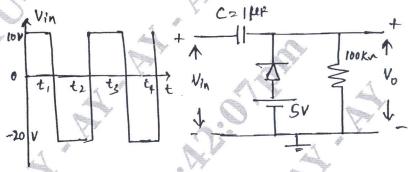


Fig.Q.1(b)

c. Derive the expression for stability factors of fixed bias circuit with respect to I<sub>CO</sub>, V<sub>BE</sub>, β and draw the circuit diagram.

OF

- 2 a. Explain the circuit of a transistor switch being used as an inverter. (06 Marks)
  - b. Determine the voltage  $V_{CE}$  and the current  $I_C$  for the voltage divider configuration Given:  $R_1 = 39 \text{K}\Omega$ ,  $R_2 = 3.9 \text{K}\Omega$ ,  $R_C = 10 \text{K}\Omega$ ,  $R_E = 1.5 \text{K}\Omega$ ,  $C_E = 50 \mu\text{F}$ , B = 100,  $V_{BE} = 0.7$ .
  - c. Sketch the output waveform for the network shown in Fig.Q.2(c). If the peak value of the a.c input if 15V and draw the transfer characteristics. (06 Marks)

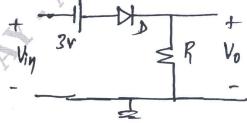


Fig.Q.2(c)

#### Module-2

- a. With a neat circuit diagram, derive an expression for Z<sub>i</sub>, Z<sub>o</sub> and A<sub>v</sub> of fixed bias circuit using r<sub>e</sub> model.
   (08 Marks)
  - b. For the Emitter follower network shown in Fig.Q.3(b). Determine re, Zi, Zo and Av.

(06 Marks)

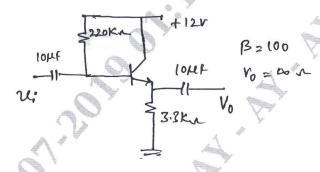


Fig.Q.3(b)

c. Prove that Miller effect of input capacitance  $C_{Mi} = (1-A_v)C_f$  and output capacitance  $C_{Mo} = \left(1 - \frac{1}{A_v}\right)C_f$ . (06 Marks)

#### OR

4 a. For the following circuit determine  $Z_i$ ,  $Z_o$ ,  $A_v$ ,  $A_i$   $h_{fb} = -0.99$ ,  $h_{ib} = 14.3\Omega$ . (08 Marks)

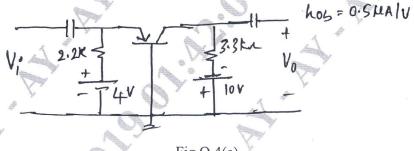


Fig.Q.4(a)

b. What are the advantages of h-parameters?

(06 Marks)

c. Define h-parameters and obtain h-parameter equivalent circuit of CE configuration.
(06 Marks)

#### Module-3

- 5 a. Obtain expression for voltage gain, current gain, input and output impedance of a Darlington Emitter follower circuit. Draw necessary equivalent circuit. (12 Marks)
  - b. With a neat block diagram, obtain expression for Z<sub>if</sub> and Z<sub>of</sub> for voltage series feedback amplifier. (08 Marks)

#### OR

6 a. Explain the general characteristics of negative feedback amplifier.

(08 Marks)

- b. Explain the need of cascading amplifier. A given amplifier arrangement has the following gains.  $Av_1 = 10$ ,  $Av_2 = 20$  and  $Av_3 = 40$ . Calculate overall voltage gain and total voltage gain in dB. (06 Marks)
- c. With a simple block diagram, explain the concept of feedback amplifier.

(06 Marks)



Module-4

- 7 a. With a neat circuit diagram, explain the operation of a class B push pull power amplifier and maximum conversion efficiency is 78.5%. (08 Marks)
  - b. With a neat circuit diagram, explain the operation of RC-phase shift oscillator using BJT and write f<sub>osc</sub> equation. (06 Marks)
  - c. A series fed class A amplifier as shown in Fig.Q.7(c). Operates from a DC source and applied sinusoidal input signal generates peak base current 9mA. Calculate I<sub>CQ</sub>, V<sub>CEQ</sub>, P<sub>dc</sub>, P<sub>ac</sub> and efficiency. (06 Marks)

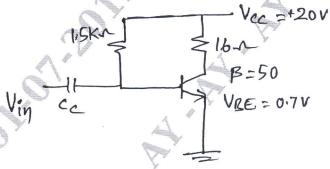


Fig.Q.7(c)

#### OR

- 8 a. The frequency selective circuit arms of wein bridge oscillator uses  $C_1 = C_2 = 0.001 \mu F$ ,  $R_1 = 10 K\Omega$  while  $R_2$  is kept variable. The frequency is to be varied from 10Hz to 50kHz by varying  $R_2$ . Find the range of  $R_2$ .
  - b. With a neat circuit diagram, explain the operation of a transformer coupled class A power amplifier and prove that conversion efficiency is 50%.

    (08 Marks)
  - c. With a neat circuit diagram, explain the working principle of crystal oscillator in series resonant mode.

    (06 Marks)

#### Module-5

- 9 a. Explain the operation of JFET amplifier using fixed bias. Draw the JFET small signal model and derive the expression for Z<sub>i</sub>, Z<sub>o</sub> and A<sub>v</sub>. (06 Marks)
  - b. Explain the construction, working and characteristics of n-channel enhancement type MOSFET. (08 Marks)
  - c. Determine the following for network shown in Fig.Q.9(c) V<sub>GSQ</sub>, V<sub>DS</sub>, V<sub>S</sub>, V<sub>G</sub>, V<sub>D</sub>. (06 Marks)

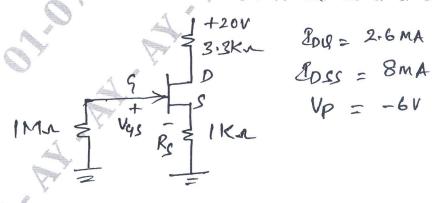


Fig.Q.9(c)

10 a. Compare FET over BJT.

(06 Marks)

b. With a neat diagrams, Explain the construction, working and characteristics of n-JFET's.

(08 Marks)

c. Design the fixed bias network as shown in Fig.Q.10(c) having an a.c. gain of 10. Determine the value of R<sub>D</sub>. (06 Marks)

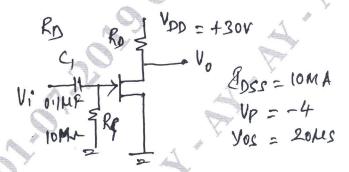


Fig.Q.10(c)